



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

HS13002

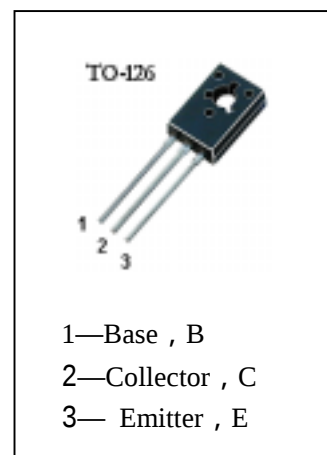
HIGH VOLTAGE SWITCH MODE APPLICATIONS

High Speed Switching

Suitable for Switching Regulator and Montor Control

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	Storage Temperature.....	-55~150
T_j	Junction Temperature.....	150
P_C	Collector Dissipation.....	10W
V_{CBO}	Collector-Base Voltage.....	600V
V_{CEO}	Collector-Emitter Voltage.....	400V
V_{EBO}	Emitter-Base Voltage.....	9V
I_C	Collector Current.....	0.25A



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	600			V	$I_C=1mA, I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	400			V	$I_C=10mA, I_B=0$
BV_{EBO}	Emitter-Base Breakdown Voltage	9			V	$I_E=1mA, I_C=0$
I_{CBO}	Collector Cut-off Current			100	μA	$V_{CB}=500V, I_E=0$
I_{EBO}	Emitter-Base Cut-off Current			100	μA	$V_{EB}=9V, I_C=0$
h_{FE}	DC Current Gain	10		40		$V_{CE}=10V, I_C=20mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0.6	V	$I_C=100mA, I_B=20mA$
$V_{BE(sat)}$	Base-Emitter Saturation Voltage			1.2	V	$I_C=100mA, I_B=20mA$
f_T	Current Gain-Bandwidth Product	8			MHZ	$V_{CE}=10V, I_C=20mA$

h_{FE} Classification

H1	H2	H3	H4	H5
10-16	14-21	19-26	24-31	29-40